

# DATASHEET

|                             |                                  |
|-----------------------------|----------------------------------|
| <b>Module TYPE</b>          | <b>DDR2 1GB/512MB<br/>SODIMM</b> |
| <b>Module speed</b>         | <b>PC-6400</b>                   |
| <b>CAS Latency</b>          | <b>CL-6</b>                      |
| <b>Pin</b>                  | <b>200pin</b>                    |
| <b>SDRAM Operating Temp</b> | <b>0 °C ~ 85 °C</b>              |

## 1. Features

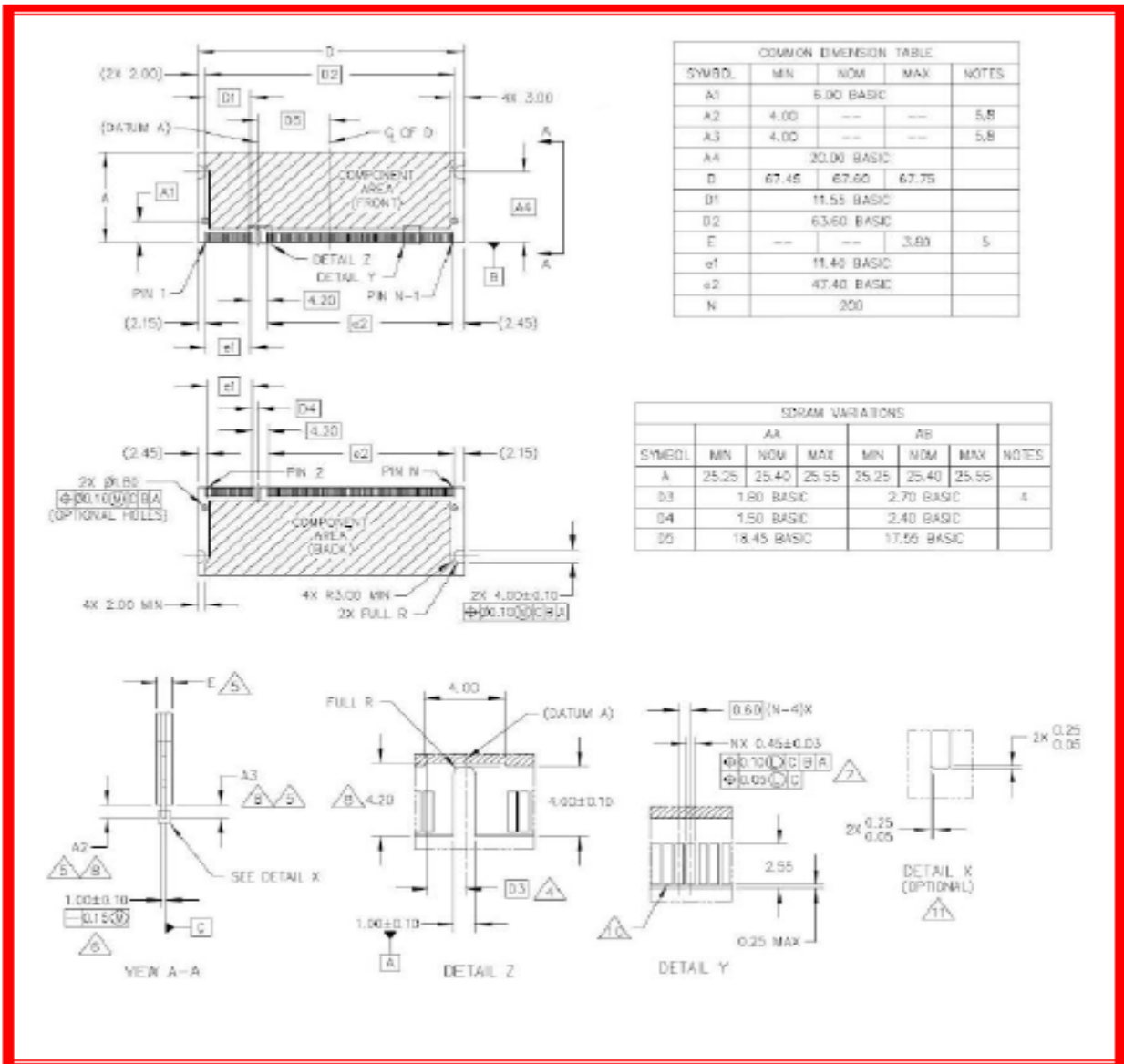
### Key Parameter

| Industry<br>Nomenclature | Speed<br>Grade | Data Rate MT/s |      |      | tRCD | tRP  | tRC  |
|--------------------------|----------------|----------------|------|------|------|------|------|
|                          |                | CL=4           | CL=5 | CL=6 | (ns) | (ns) | (ns) |
| PC2-6400                 | -              | 533            | 667  | 800  | 15   | 15   | 60   |

- JEDEC Standard 200-pin Dual In-Line Memory Module
- Intend for 400MHz applications
- Inputs and Outputs are SSTL-18 compatible
- VDD=VDDQ= 1.8 Volt  $\pm$  0.1
- Differential clock input
- All inputs are sampled at the positive going edge of the system clock
- Bi-Directional data strobe with one clock cycle preamble and one-half clock post-amble
- Address and control signals are fully synchronous to positive clock edge.
- Auto Refresh (CBR) and Self Refresh Modes support.
- Serial Presence Detect with EEPROM
- Automatic and controlled precharge commands.
- Auto & self refresh 7.8 $\mu$ s ( $T_A \leq +85^\circ\text{C}$ )
- Golden Contactor
- SDRAM Operation Temperature (*Note 1*)
  - $0^\circ\text{C} \leq T_A \leq +85^\circ\text{C}$
- Programmable Device Operation:
  - Burst Type: Sequential or Inteleave
  - Operation: Burst Read and Write
  - Device CAS# Latency: 6
  - Burst Length: 4, 8
- RoHS Compliant (*Section 15*)

*Note: 1. The refresh rate is required to double when  $T_c$  exceeds  $85^\circ\text{C}$ .*

## 2. PACKAGE DIMENSION



Note: Device position is only for reference.